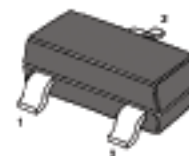


NPN Silicon Epitaxial Planar Transistor

for high voltage switching and amplifier applications.


 1. Base 2. Emitter 3. Collector
 SOT-23 Plastic Package

Absolute Maximum Ratings ($T_a = 25\text{ }^\circ\text{C}$)

Parameter	Symbol	Value	Unit
Collector Base Voltage	V_{CBO}	500	V
Collector Emitter Voltage	V_{CEO}	400	V
Emitter Base Voltage	V_{EBO}	6	V
Collector Current	I_C	300	mA
Power Dissipation	P_{tot}	200	mW
Junction Temperature	T_j	150	$^\circ\text{C}$
Storage Temperature Range	T_{stg}	- 55 to + 150	$^\circ\text{C}$

Characteristics at $T_a = 25\text{ }^\circ\text{C}$

Parameter	Symbol	Min.	Max.	Unit
DC Current Gain				
at $V_{CE} = 10\text{ V}$, $I_C = 1\text{ mA}$	h_{FE}	40	-	-
at $V_{CE} = 10\text{ V}$, $I_C = 10\text{ mA}$	h_{FE}	50	200	-
at $V_{CE} = 10\text{ V}$, $I_C = 50\text{ mA}$	h_{FE}	45	-	-
at $V_{CE} = 10\text{ V}$, $I_C = 100\text{ mA}$	h_{FE}	40	-	-
Collector Base Cutoff Current at $V_{CB} = 400\text{ V}$	I_{CBO}	-	0.1	μA
Collector Emitter Cutoff Current at $V_{CE} = 400\text{ V}$	I_{CEO}	-	0.5	μA
Emitter Base Cutoff Current at $V_{EB} = 4\text{ V}$	I_{EBO}	-	0.1	μA
Collector Base Breakdown Voltage at $I_C = 100\text{ }\mu\text{A}$	$V_{(BR)CBO}$	500	-	V
Collector Emitter Breakdown Voltage at $I_C = 1\text{ mA}$	$V_{(BR)CEO}$	400	-	V
Emitter Base Breakdown Voltage at $I_E = 100\text{ }\mu\text{A}$	$V_{(BR)EBO}$	6	-	V
Collector Emitter Saturation Voltage				
at $I_C = 1\text{ mA}$, $I_B = 0.1\text{ mA}$	$V_{CE(sat)}$	-	0.4	V
at $I_C = 10\text{ mA}$, $I_B = 1\text{ mA}$	$V_{CE(sat)}$	-	0.5	V
at $I_C = 50\text{ mA}$, $I_B = 5\text{ mA}$	$V_{CE(sat)}$	-	0.75	V
Base Emitter Saturation Voltage at $I_C = 10\text{ mA}$, $I_B = 1\text{ mA}$	$V_{BE(sat)}$	-	0.75	V
Collector Output Capacitance at $V_{CB} = 20\text{ V}$, $f = 1\text{ MHz}$	C_{ob}	-	7	pF

